/ Descriptions

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

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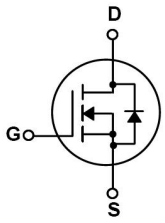
Low gate charge, low crss, fast switching.

/ Applications

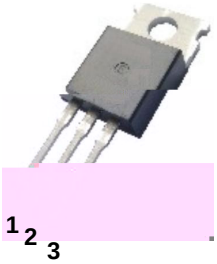
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

/ h_{FE} Classifications & Marking

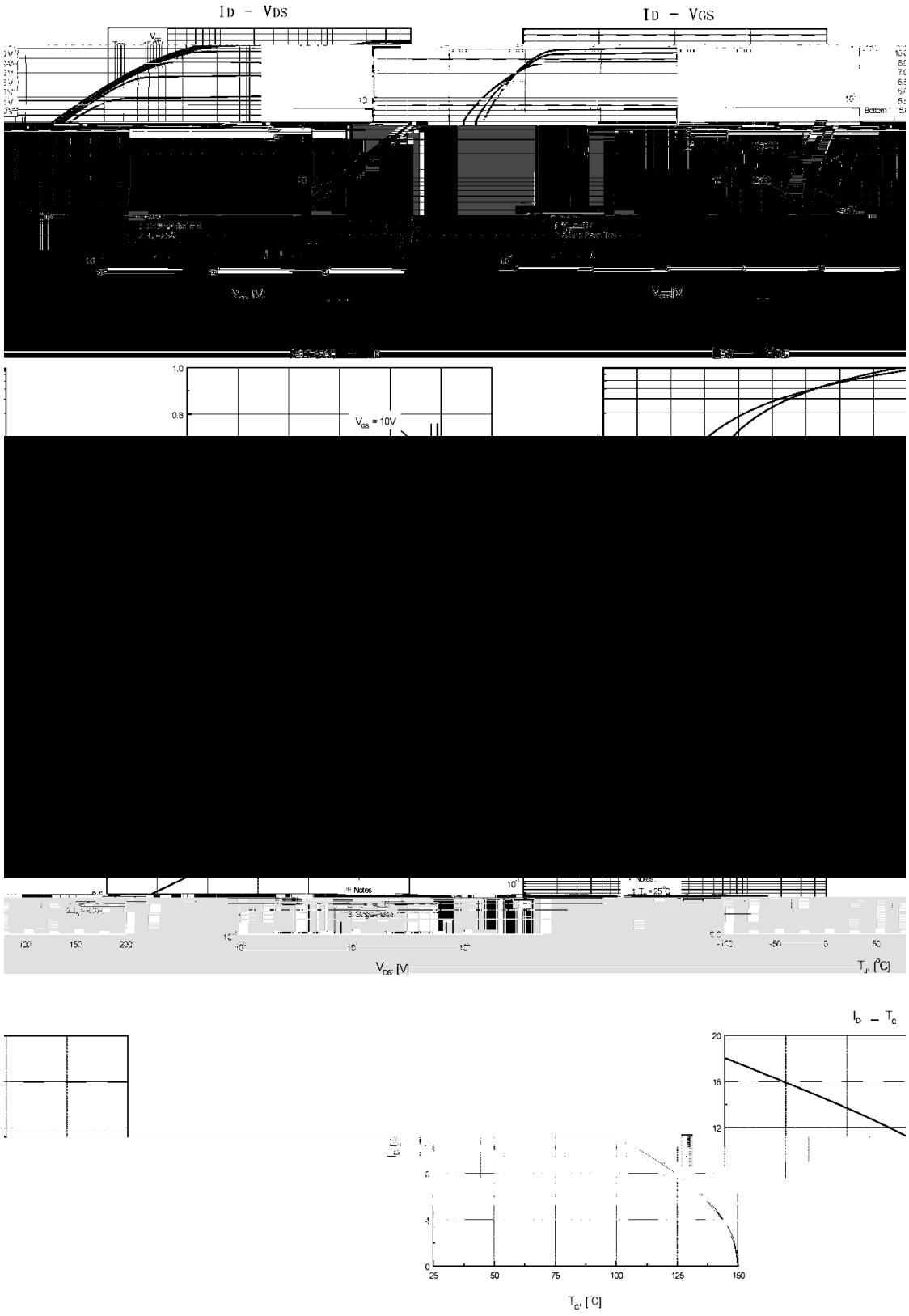
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	200	V
Drain Current	I_D(Tc=25)	18	A
	I_D(Tc=100)	11.4	A
Pulsed Drain Current	I_{DM}	72	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	250	mJ
Repetitive Avalanche Energy	E_{AR}	13.9	mJ
Avalanche Current	I_{AR}	18	A
Total Power Dissipation	P_D(Tc=25)	139	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

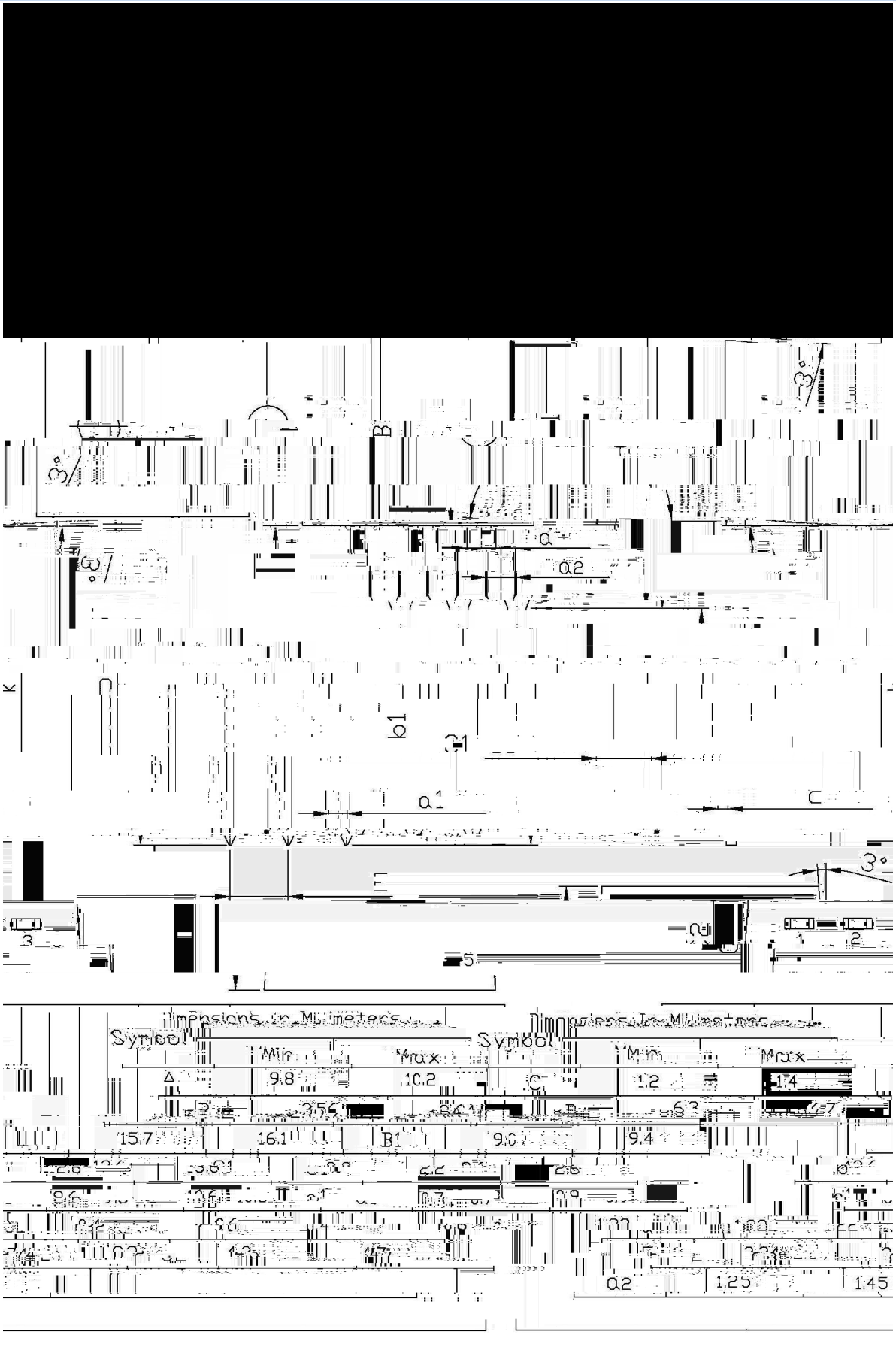
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	BV_{DSS}	V_{GS}=0V I_D=250 A	200			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V V_{GS}=0V			10	A
		V_{DS}=160V T_C=125			100	A
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±30V V_{DS}=0V			±0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250 A	2.0		4.0	V
Forward Transconductance	g_{FS}	V_{DS}=40V I_D=9.0A		13		S

Static Drain-Source
ARC.s8(So8(.02 0 .26 552 Tc.02 0 0 7.02 23R.5 334.5804 Tm-.0001f5527JE9 Tw[S)4910.5 283(on66.34 314.3004 T

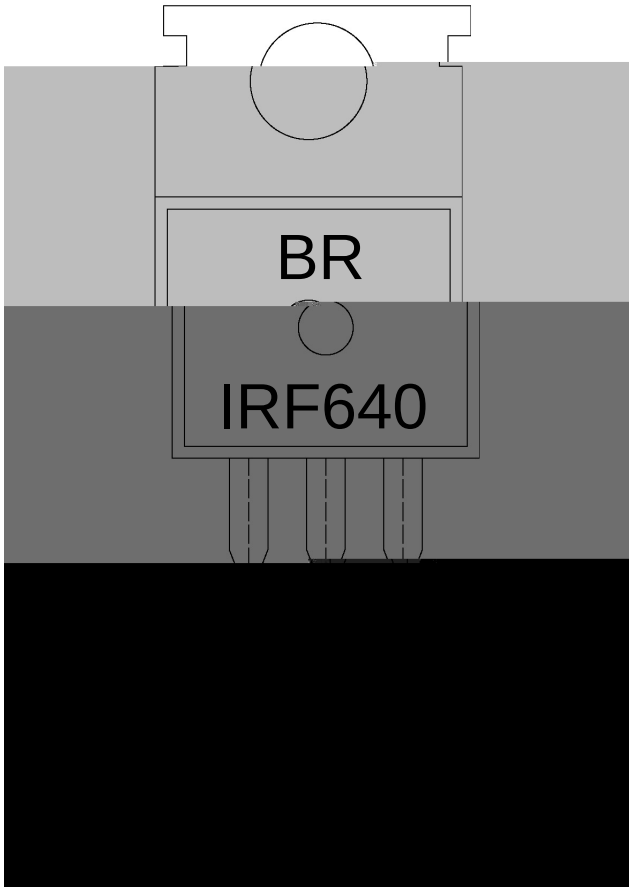
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

IRF640

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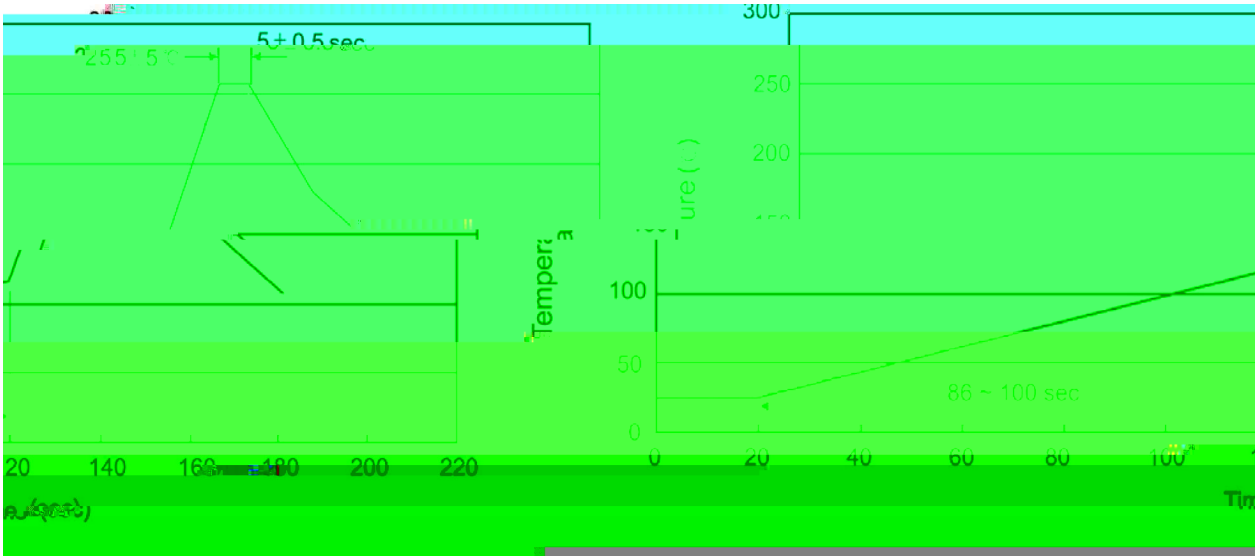
Note:

BR:	Company Code
IRF640:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



						Note:	
1		25	150		60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5				5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3				2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

3

/ TUBE

3

/ Notices